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View Online at https://aerobasegroup.com/nsn/5961-01-275-8268

Inclosure Material:

Metal all transistor

Overall Length:

0.210 inches all transistor

Terminal Length:

0.500 inches all transistor

Overall Diameter:

0.230 inches all transistor

Internal Configuration:

Junction contact all transistor

Internal Junction Configuration:

Npn all transistor

Component Function Relationship:

Matched

Component Name And Quantity:

3 transistor

Mounting Method:

Terminal all transistor

Terminal Circle Diameter:

0.100 inches all transistor

Features Provided:

Hermetically sealed case

Semiconductor Material:

Silicon all transistor

Voltage Rating In Volts Per Characteristic:

30.0 collector to base voltage/static/emitter open all transistor and 15.0 collector to emitter voltage/static/base open all transistor and 2.5 emitter to base voltage, static, collector open all transistor

Current Rating Per Characteristic:

10.00 microamperes source cutoff current all transistor

Power Rating Per Characteristic:

300.0 milliwatts small-signal input power, common-collector preset all transistor

Transfer Ratio:

10.0 static forward current transfer ratio, common-emitter all transistor and 19.0 static forward current transfer ratio, common-emitter all transistor

Maximum Operating Tempurature Per Measurement Point:

200.0 degrees celsius junction all transistor

Terminal Type And Quantity:

4 uninsulated wire lead all transistor

Shelf Life:

N/a

Unit Of Measure:

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- **Demilitarization:**

No

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